

## **isc Silicon NPN Power Transistor**

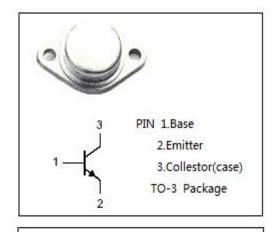
# **BU626A**

### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub> = 400V(Min.)
- · Low Collector-Emitter Saturation Voltage-
  - : V<sub>CE(sat)</sub> = 3.3V(Max.) @ I<sub>C</sub>= 8A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **APPLICATIONS**

• Designed for use in power supply units of TV receivers.

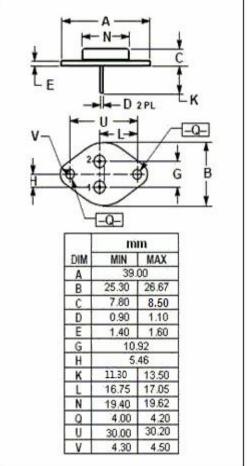


## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	1000	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	٧
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	10	Α
I <sub>CM</sub>	Collector Current-Peak	15	Α
Pc	Collector Power Dissipation @ $T_c$ =25 $^{\circ}$ C	100	W
TJ	Junction Temperature 150		$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.5	°C/W





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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	400			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 2.5A			3.3	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 2.5A			2.2	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1000V; V <sub>BE</sub> = 0			1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 10A; V <sub>CE</sub> = 1.5V	10			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 2.5A; V <sub>CE</sub> = 10V	15			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V	6			MHz
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 8A; I <sub>B1</sub> = -I <sub>B2</sub> = 2.5A			1.0	μS

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